P-Channel 100-V (D-S) MOSFET

Key Features:

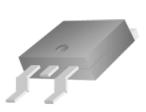
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

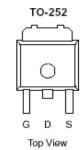
Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)	
-100	80 @ V _{GS} = -10V	-20	
	86 @ V _{GS} = -4.5V	-19	







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage			-100	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current a	T _C =25°C	I_D	I _D -20		
Pulsed Drain Current ^b		I _{DM}	-80	Α	
Continuous Source Current (Diode Conduction) a	T _C =25°C	I _S	-20	Α	
Power Dissipation ^a	T _C =25°C	P_D	50	W	
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Maximum	Units	
Maximum Junction-to-Ambient °	$R_{\theta JA}$	40	°C/W	
Maximum Junction-to-Case	$R_{ heta JC}$	3	C/VV	

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Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

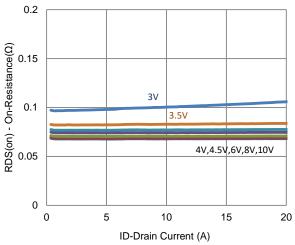
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	l	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}$			-1		
Zero Gate Voltage Diain Current	I _{DSS}	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-25			Α	
Drain Course On Besistance a	r	$V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}$			80	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -8 \text{ A}$			86		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -10 \text{ A}$		24		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -10 \text{ A}, V_{GS} = 0 \text{ V}$		-0.87		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = -50 \text{ V}, V_{GS} = -4.5 \text{ V},$		37			
Gate-Source Charge	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -10 \text{ A}$		15		nC	
Gate-Drain Charge	Q_gd	10 - 10 //		11			
Turn-On Delay Time	t _{d(on)}	V 50 V D = 5 O		10			
Rise Time	t _r	$V_{DS} = -50 \text{ V}, R_{L} = 5 \Omega,$ $I_{D} = -10 \text{ A},$		9		nc	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		96		ns	
Fall Time	t _f	VGEN - 10 V, NGEN 0 12		27			
Input Capacitance	C _{iss}			3520			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$	_	167		рF	
Reverse Transfer Capacitance	C _{rss}	7		71			

Notes

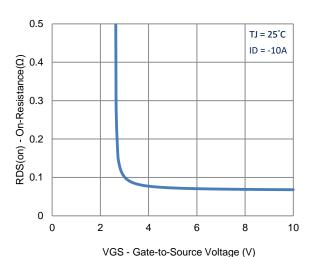
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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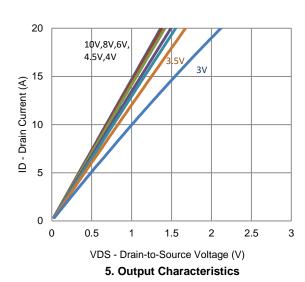
Typical Electrical Characteristics

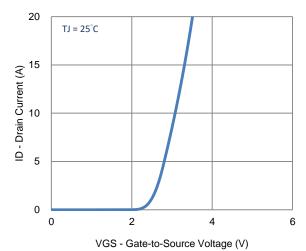


1. On-Resistance vs. Drain Current

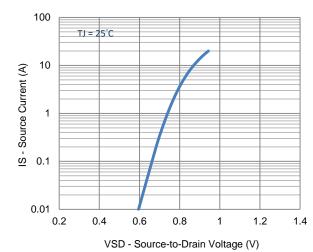


3. On-Resistance vs. Gate-to-Source Voltage

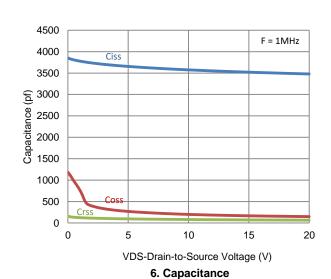




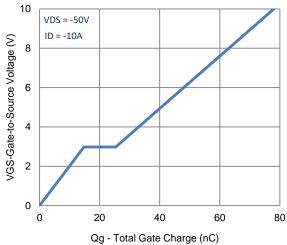


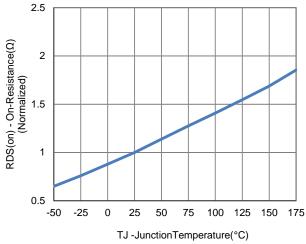


4. Drain-to-Source Forward Voltage



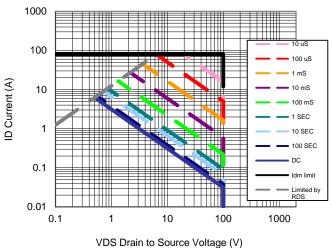
Typical Electrical Characteristics

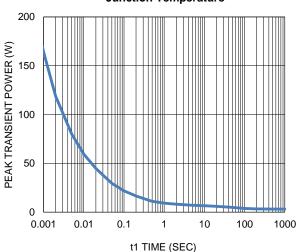






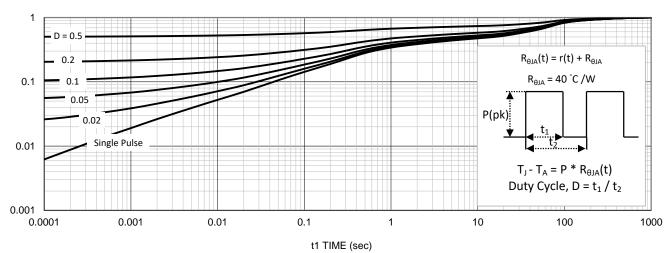






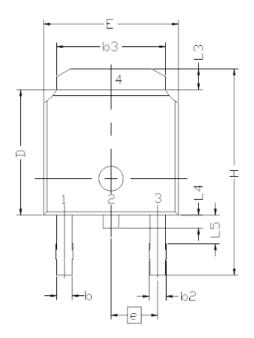
9. Safe Operating Area

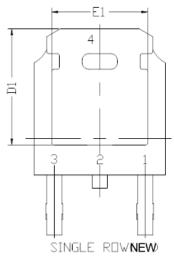
10. Single Pulse Maximum Power Dissipation

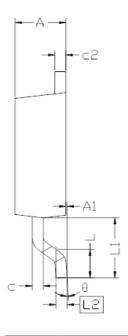


11. Normalized Thermal Transient Junction to Ambient

Package Information







CVMDDI	DIMENS:		REQMTS
SYMBOL	MIN	NDM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1		.743 RI	
L2		.508 BS	
L3	0,89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0,88
b2	0.77	0.84	1.14
b3	5,21	5.34	5.46
е		286 BS	
Α	2,20	2,30	2.38
A1	0		0.127
C	0.45	0.50	0.60
c2	0.45	0,50	0.58
D1	5.30		
E1	4.40		
θ	0°		10°

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.